

**isc Silicon NPN Power Transistor**
**2SC4159**
**DESCRIPTION**

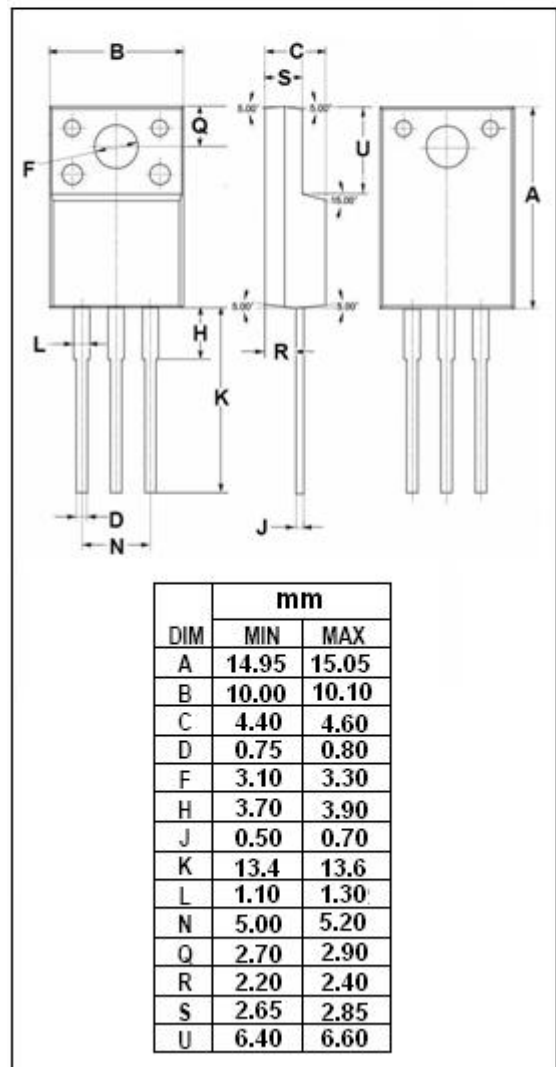
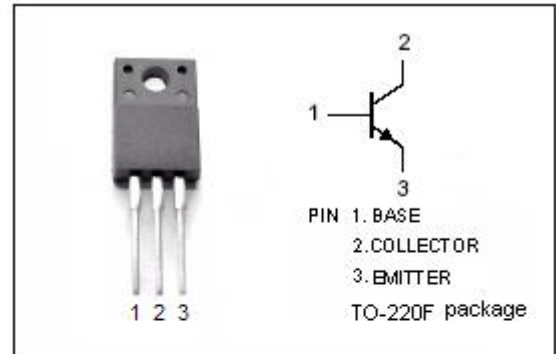
- High Collector-Emitter Breakdown Voltage-  
 $V_{(BR)CEO} = 160V$  (Min)
- Large Current Capacity
- Complement to Type 2SA1606
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

- Designed for high-voltage switching, AF power amplifier, 100W output predrivers.

**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	180	V
$V_{CEO}$	Collector-Emitter Voltage	160	V
$V_{EBO}$	Emitter-Base Voltage	6.0	V
$I_C$	Collector Current-Continuous	1.5	A
$I_{CM}$	Collector Current-Peak	3	A
$P_C$	Total Power Dissipation @ $T_C=25^\circ\text{C}$	15	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$



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**ELECTRICAL CHARACTERISTICS**

 T<sub>c</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 1mA; I <sub>E</sub> = 0	180			V
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 1mA; R <sub>BE</sub> = ∞	160			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 1mA; I <sub>C</sub> = 0	6			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 500mA; I <sub>B</sub> = 50mA		0.3		V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 10mA; V <sub>CE</sub> = 5V			1.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 120V; I <sub>E</sub> = 0			10	μ A
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 4V; I <sub>C</sub> = 0			10	μ A
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 300mA; V <sub>CE</sub> = 5V	60		200	
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 50mA; V <sub>CE</sub> = 10V		100		MHz
C <sub>OB</sub>	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 10V; f= 1.0MHz		23		pF

**Switching Times**

t <sub>on</sub>	Turn-on Time	I <sub>C</sub> = 0.5A, R <sub>L</sub> = 40 Ω, I <sub>B1</sub> = -I <sub>B2</sub> = 50mA, V <sub>CC</sub> = -20V; P <sub>W</sub> = 20 μ s		0.15		μ s
t <sub>stg</sub>	Storage Time			0.81		μ s
t <sub>f</sub>	Fall Time			0.48		μ s

**◆ h<sub>FE</sub> Classifications**

D	E
60-120	100-200

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